

Symbol	Parameter	Test Conditions	Values	Unit
V_R	Maximum D.C. Reverse Voltage		1200	V
V_{RRM}	Maximum Repetitive Reverse Voltage		1200	V
$I_{F(AV)}$	Average Forward Current	T_C=100℃, Per Diode	100	A
		T_C=100℃, Per Moudle	200	A
$I_{F(RMS)}$	RMS Forward Current	T_C=100℃, Per Diode	150	A
I_{FSM}	Non-Repetitive Surge Forward Current	T_J=45℃, t=10ms, 50Hz, Sine	1100	A
		60Hz, Sine	1200	A
I^2t	I^2t (For Fusing)	T_J=45℃, t=10ms, 50Hz, Sine	6060	A^2s

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{RM}	Reverse Leakage Current	V_R=1200V	--	--	0.5	mA
		V_R=1200V, T_J=125℃	--	--	8	mA
V_F	Forward Voltage	I_F=100A	--	1.6	--	V
		I_F=100A, T_J=125℃	--	1.4	--	V
t_{rr}	Reverse Recove ry Time	I_F=1A, V_R=30V, di_F/dt=-200A/μs	--	55	--	ns
t_{rr}	Reverse Recove ry Time	V_R=600V, I_F=100A	--	135	--	ns
I_{RRM}	Max. Reverse Recovery Current	di_F/dt=-200A/μs, T_J=25℃	--	10	--	A
t_{rr}	Reverse Recovery Time	V_R=600V, I_F=100A	--	380	--	ns
I_{RRM}	Max. Reverse Recovery Curren	di_F/dt=-200A/μs, T_J=125℃	--	21	--	A

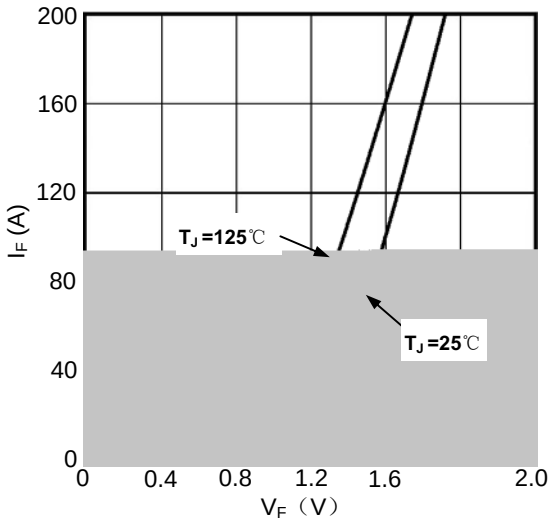


Figure1. Forward Voltage Drop vs Forward Current

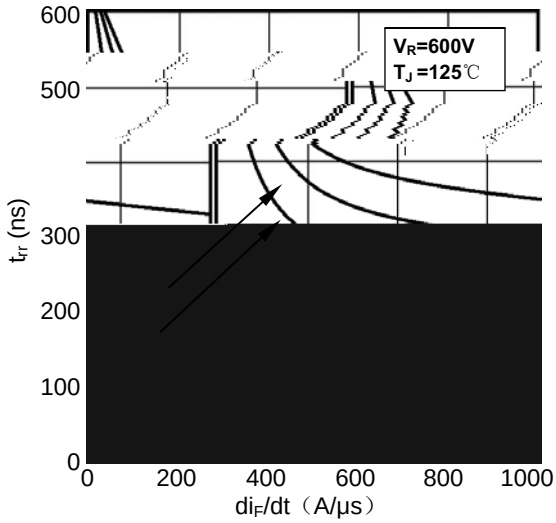


Figure2. Reverse Recovery Time vs di_F/dt

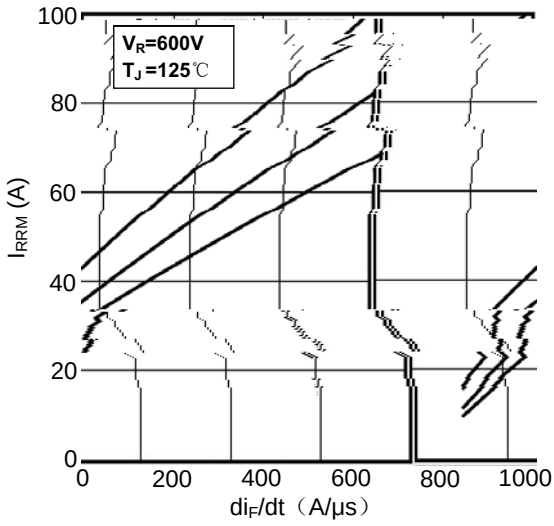


Figure3. Reverse Recovery Current vs di_F/dt

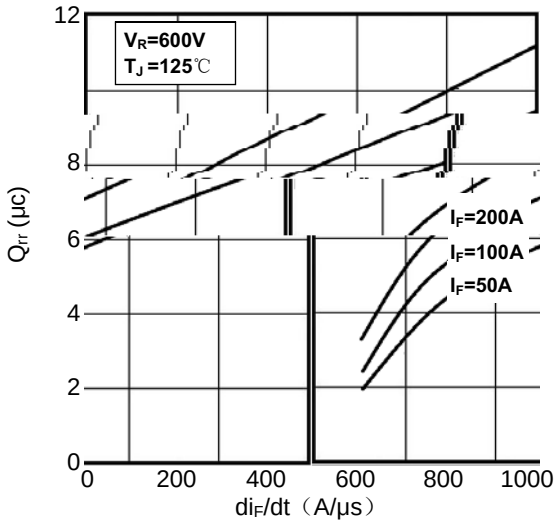


Figure4. Reverse Recovery Charge vs di_F/dt

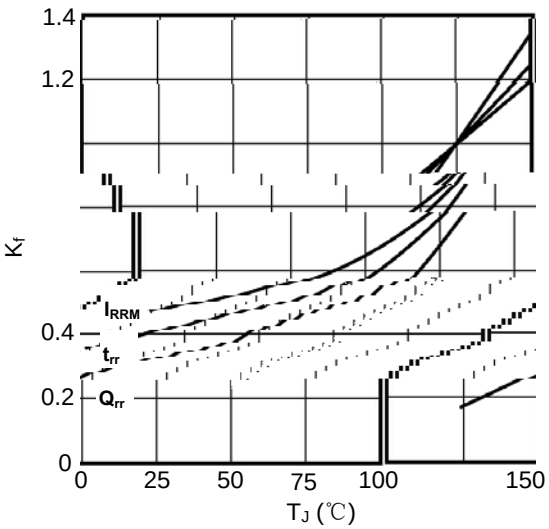


Figure5. Dynamic Parameters vs Junction Temperature

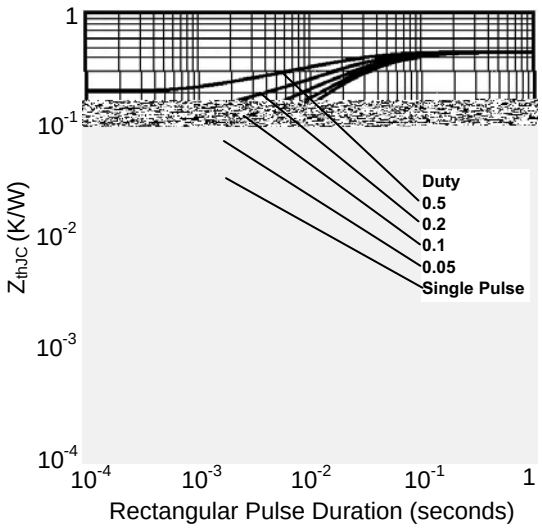


Figure6. Transient Thermal Impedance

